

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning at page 12, line 22, as follows:

As illustrated in Figures 1(a) to 1(d), each of the side plates 3a of the storage container main body 1 has a plurality of holding members [[6]] 5 for holding in parallel a plurality of flexible substrates 4 in a shape of a curve so that the flexible substrates 4 do not contact each other when stored at stand position.

Please amend the paragraph beginning at page 14, last line, as follows:

On two substrates 4 made of plastic, formed are silicone nitride films generally adopted as gate insulating films or protective films of amorphous ~~silicone~~ silicon TFT (Thin Film Transistor) liquid crystal display. Incidentally, the ~~silicone~~ silicon nitride films are formed at a temperature of 200 °C using the plasma CVD method. The ~~silicone~~ silicon nitride film has a thickness of 350 nm formed by this method has a membrane stress (tensile stress) of +270 Mpa.